IN THE CLAIMS:

The following is a listing of the claims in the present application with claims 1, 3, 8 and 14 shown as currently amended.

1. (Currently Amended) A method for preparing a ~~film structure of a~~ ferroelectric single crystal~~,~~ film structure comprising the steps of ~~which comprises adhering a ferroelectric single crystal plate to a substrate by a conductive adhesive, wherein the ferroelectric single crystal is a material having the composition of formula (I)~~:

~~x(A)y(B)z(C) p(P)n(N) (I)~~

~~wherein~~

~~is Pb(Mg1/3Nb2/3)03 or Pb(Zn1/3Nb2/3)03,~~

~~is PbTiO3,~~

~~is LiTa03,~~

~~(P) is a metal selected from the group consisting of Pt, Au, Ag, Pd and Rh,~~

~~(N) is an oxide of a metal selected from the group consisting of Ni, Co, Fe, Sr, Sc, Ru, Cu and Cd,~~

~~x is a number in the range of 0.65 to 0.98,~~

~~y is a number in the range of 0.01 to 0.34,~~

~~z is a number in the range of 0.01 to 0.1, and~~

~~p and n are each independently a number in the range of 0.01 to 5,~~

~~wherein the conductive adhesive is a gold or silver containing epoxy paste, or a Pt containing adhesive sol~~.

preparing a ferroelectric single crystal plate and a silicon substrate, separately;

forming a silicon dioxide layer on the silicon substrate;

applying a heat-curable conductive adhesive layer on the silicon dioxide layer;

laminating the single crystal plate on the adhesive layer;

curing the adhesive layer by heat treatment to form a bottom electrode layer;

polishing the single crystal plate to form a ferroelectric single crystal film;

forming a top electrode layer on the single crystal film;

polarizing the single crystal film to obtain a polarized ferroelectric single crystal layer; and

etching the substrate, the top and bottom electrodes and the polarized single crystal layer in a desired pattern.

2. (Previously Amended) The method of claim 1, wherein the single crystal plate is polished to a thickness of 1 to 100 μm before and after the adhesion with the substrate.

3. (Currently Amended) The method of claim 1, wherein ~~the single crystal plate is adhered to the substrate by placing a conductive adhesive between the single crystal plate and the substrate and heat treating the resulting laminate containing the adhesive~~ the adhesive layer is cured by heat treatment at a temperature ranging from room temperature to 150 °C for 1 to 24 hours ~~to cure the adhesive~~.

4 - 7 (Cancelled).

8. (Currently Amended) The method of claim 1, wherein the ferroelectric single crystal film structure has a dielectric constant of 1,000 or greater ~~as measured in a film form~~.

9. (Cancelled).

10. (Original) The method of claim 1, wherein the substrate comprises a layer of an oxide material selected from SiO_2, MgO, Al_2O_3 and ZnO, the oxide layer being contacted with the conductive adhesive layer.

11. (Original) The method of claim 1, which further comprises forming a conductive metal layer on the surface of the single crystal plate opposite to the adhesive layer by a sputtering or an electronic beam evaporation method.

12 - 13. (Cancelled).

14. (New) The method of claim 1, wherein the ferroelectric single crystal film structure is a material having the composition of formula (I):

$$x(A)y(B)z(C)\text{-}p(P)n(N) \qquad (I)$$

wherein,

(A) is $Pb(Mg_{1/3}Nb_{2/3})O_3$ or $Pb(Zn_{1/3}Nb_{2/3})O_3$,

(B) is $PbTiO_3$,

(C) is $LiTaO_3$,

(P) is a metal selected from the group consisting of Pt, Au, Ag, Pd and Rh,

(N) is an oxide of a metal selected from the group consisting of Ni, Co, Fe, Sr, Sc, Ru, Cu and Cd,

x is a number in the range of 0.65 to 0.98,

y is a number in the range of 0.01 to 0.34,

z is a number in the range of 0.01 to 0.1, and

p and n are each independently a number in the range of 0.01 to 5.